

MCL-SS355

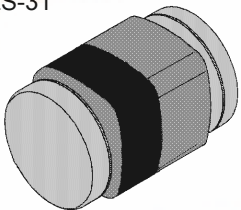
Silicon Epitaxial Planar Switching Diode

High-speed switching applications

Features

- Fits onto SOD-323 / SOT-23 footprints
- High reliability with high surge current handling capability.

LS-31



Glass Case MicroMELF

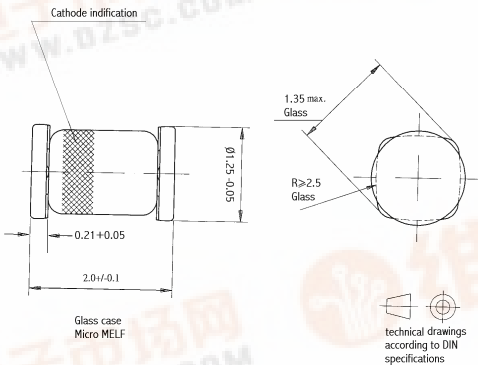
Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V _{RM}	90	V
Reverse Voltage	V _R	80	V
Average Rectified Forward Current	I _{F(AV)}	100	mA
Peak Forward Current	I _{FM}	225	mA
Surge Forward Current (1 s)	I _{FSM}	500	mA
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 100 mA	V _F	1.2	V
Reverse Current at V _R = 80 V	I _R	0.1	μA
Diode Capacitance at V _R = 0.5 V, f = 1 MHz	C _d	3	pF
Reverse Recovery Time at I _F = 10 mA, V _R = 6 V, R _L = 100 Ω	t _{rr}	4	ns

Dimensions in mm



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



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ELECTRICAL CHARACTERISTIC CURVES ($T_a=25^\circ\text{C}$)

Fig. 1- FORWARD CHARACTERISTICS

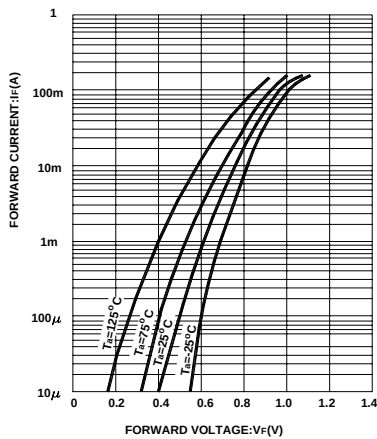


Fig. 2- REVERSE CHARACTERISTICS

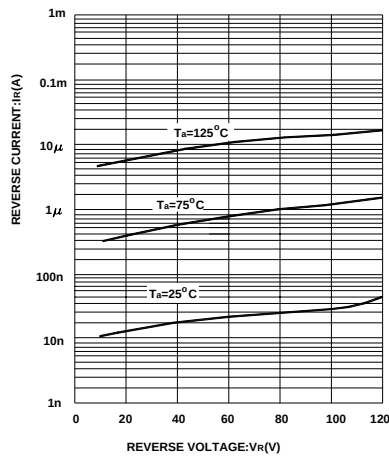


Fig. 3- CAPACITANCE BETWEEN TERMINALS CHARACTERISTICS

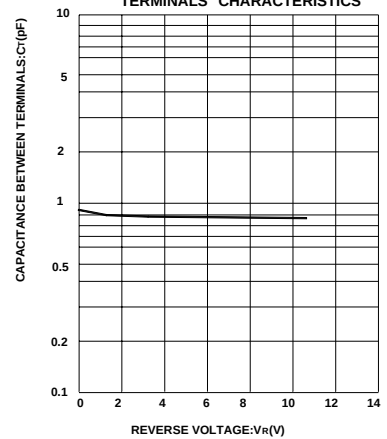


Fig. 4- REVERSE RECOVERY TIME CHARACTERISTICS

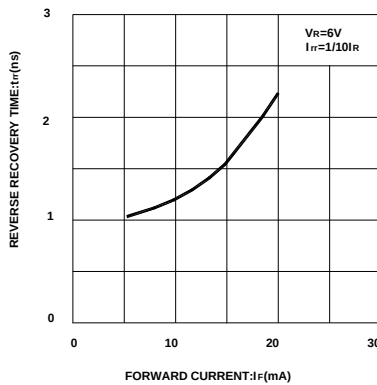


Fig. 5- SURGE CURRENT CHARACTERISTICS

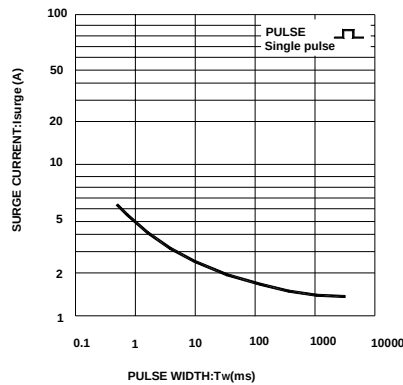
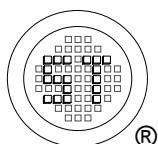
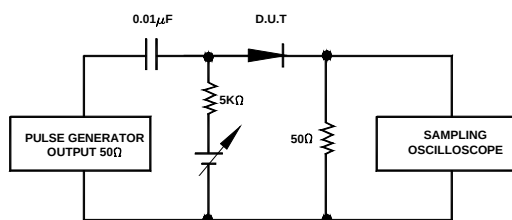


Fig. 6- REVERSE RECOVERY TIME(t_{rr}) MEASUREMENT CIRCUIT



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